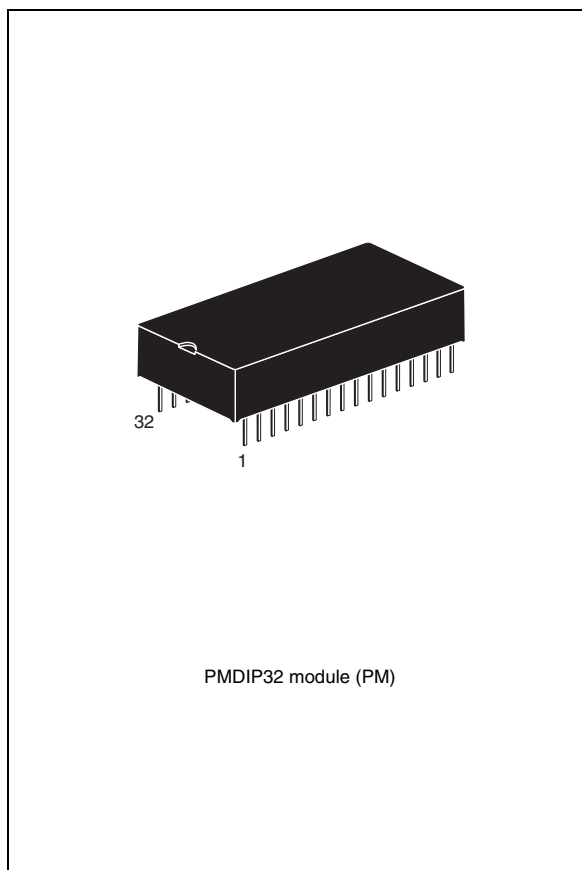

5.0 or 3.3 V, 4 Mbit (512 Kbit x 8) TIMEKEEPER[®] SRAM

Features

- Integrated ultra low power SRAM, real-time clock, power-fail control circuit, battery, and crystal
- BCD coded year, month, day, date, hours, minutes, and seconds
- Automatic power-fail chip deselect and WRITE protection
- WRITE protect voltages: (V_{PFD} = Power-fail deselect voltage)
 - M48T512Y: $V_{\text{CC}} = 4.5$ to 5.5 V
 4.2 V $\leq V_{\text{PFD}} \leq 4.5$ V
 - M48T512V: $V_{\text{CC}} = 3.0$ to 3.6 V
 2.7 V $\leq V_{\text{PFD}} \leq 3.0$ V
(contact ST sales office for availability)
- Conventional SRAM operation; unlimited WRITE cycles
- Software controlled clock calibration for high accuracy applications
- 10 years of data retention and clock operation in the absence of power
- Pin and function compatible with industry standard 512 K x 8 SRAMS
- Self-contained battery and crystal in DIP package
- RoHS compliant
 - Lead-free second level interconnect



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1 Description

The M48T512Y/V TIMEKEEPER® RAM is a 512 Kb x 8 non-volatile static RAM and real-time clock organized as 524,288 words by 8 bits. The special DIP package provides a fully integrated battery-backed memory and real-time clock solution.

The M48T512Y/V directly replaces industry standard 512 Kb x 8 SRAMs. It also provides the non-volatility of Flash without any requirement for special WRITE timing or limitations on the number of WRITES that can be performed.

Figure 1. Logic diagram

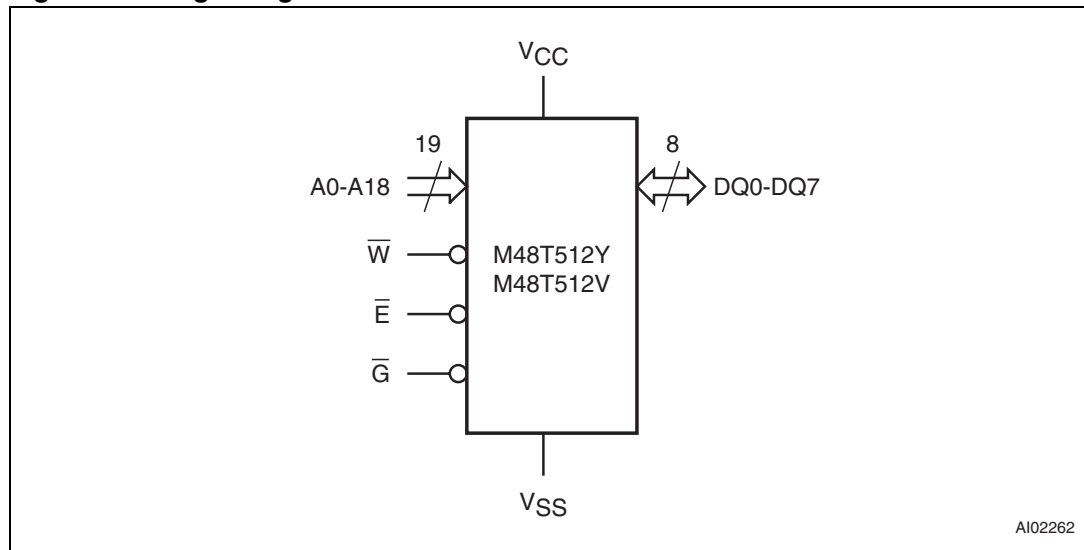


Table 1. Signal names

| | |
|-----------------|-----------------------|
| A0-A18 | Address inputs |
| DQ0-DQ7 | Data inputs / outputs |
| \bar{E} | Chip enable input |
| \bar{G} | Output enable input |
| \bar{W} | WRITE enable input |
| V _{CC} | Supply voltage |
| V _{SS} | Ground |

Figure 2. 32-pin DIP connections

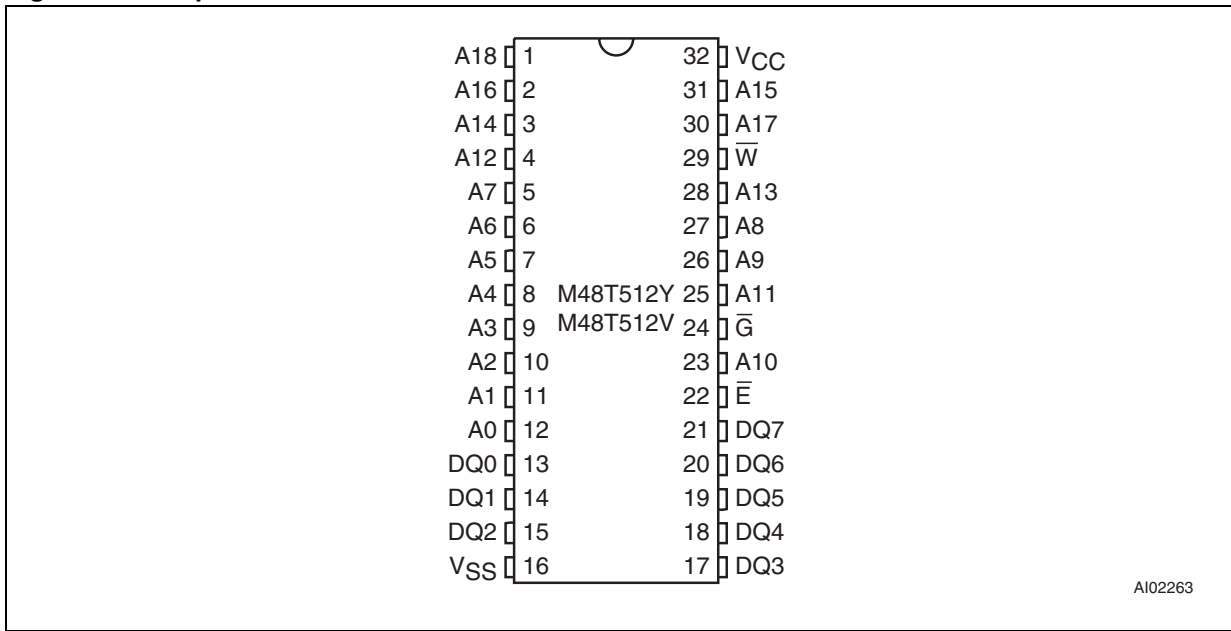
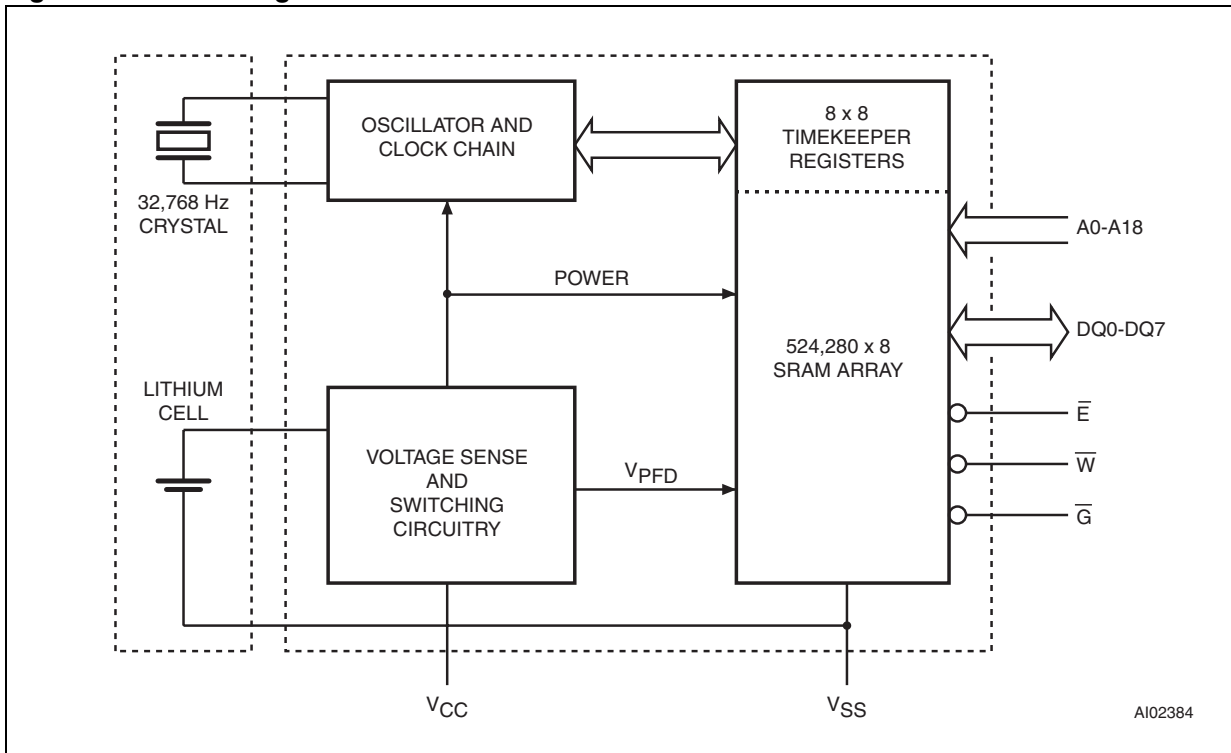


Figure 3. Block diagram



2 Operating modes

The 32-pin, 600 mil hybrid DIP houses a controller chip, SRAM, quartz crystal, and a long life lithium button cell in a single package. [Figure 3 on page 6](#) illustrates the static memory array and the quartz controlled clock oscillator. The clock locations contain the year, month, date, day, hour, minute, and second in 24 hour BCD format. Corrections for 28, 29 (leap year - compliant until the year 2100), 30, and 31 day months are made automatically. Byte 7FFF8h is the clock control register (see [Table 5 on page 12](#)). This byte controls user access to the clock information and also stores the clock calibration setting. The seven clock bytes (7FFFFh-7FFF9h) are not the actual clock counters; they are memory locations consisting of BiPORT™ READ/WRITE memory cells within the static RAM array. The M48T512Y/V includes a clock control circuit which updates the clock bytes with current information once per second. The information can be accessed by the user in the same manner as any other location in the static memory array. The M48T512Y/V also has its own power-fail detect circuit. This control circuitry constantly monitors the supply voltage for an out of tolerance condition. When V_{CC} is out of tolerance, the circuit write protects the TIMEKEEPER register data and SRAM, providing data security in the midst of unpredictable system operation. As V_{CC} falls, the control circuitry automatically switches to the battery, maintaining data and clock operation until valid power is restored.

Table 2. Operating modes

| Mode | V_{CC} | \bar{E} | \bar{G} | \bar{W} | DQ0-DQ7 | Power |
|----------|------------------------------------|-----------|-----------|-----------|-----------|---------------------|
| Deselect | 4.5 to 5.5 V or 3.0 to 3.6 V | V_{IH} | X | X | High Z | Standby |
| WRITE | | V_{IL} | X | V_{IL} | D_{IN} | Active |
| READ | | V_{IL} | V_{IL} | V_{IH} | D_{OUT} | Active |
| READ | | V_{IL} | V_{IH} | V_{IH} | High Z | Active |
| Deselect | V_{SO} to $V_{PFD}(\min)^{(1)}$ | X | X | X | High Z | CMOS standby |
| Deselect | $\leq V_{SO}^{(1)}$ | X | X | X | High Z | Battery backup mode |

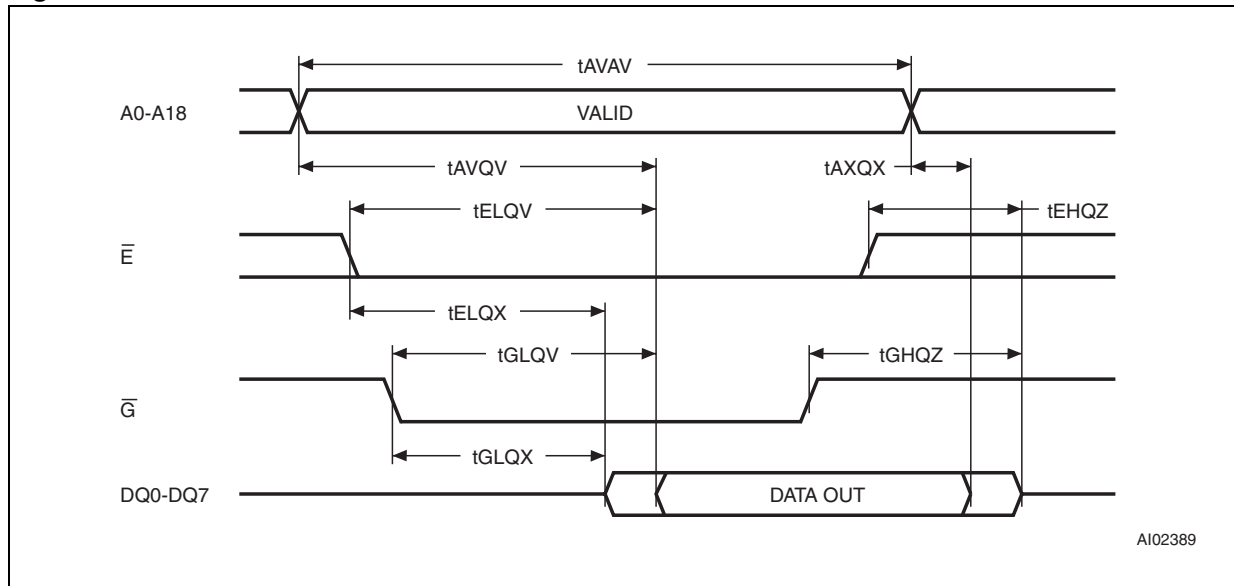
1. See [Table 11 on page 18](#) for details.

Note: $X = V_{IH}$ or V_{IL} ; V_{SO} = Battery backup switchover voltage.

2.1 READ mode

The M48T512Y/V is in the READ mode whenever \bar{W} (WRITE enable) is high and \bar{E} (chip enable) is low. The unique address specified by the 19 address inputs defines which one of the 524,288 bytes of data is to be accessed. Valid data will be available at the data I/O pins within address access time (t_{AVQV}) after the last address input signal is stable, providing the \bar{E} and \bar{G} access times are also satisfied. If the \bar{E} and \bar{G} access times are not met, valid data will be available after the latter of the chip enable access times (t_{ELQV}) or output enable access time (t_{GLQV}). The state of the eight three-state data I/O signals is controlled by \bar{E} and \bar{G} . If the outputs are activated before t_{AVQV} , the data lines will be driven to an indeterminate state until t_{AVQV} . If the address inputs are changed while \bar{E} and \bar{G} remain active, output data will remain valid for output data hold time (t_{AXQX}) but will go indeterminate until the next address access.

Figure 4. READ mode AC waveforms



Note: $\overline{WE} = High$.

Table 3. READ mode AC characteristics

| Symbol | Parameter ⁽¹⁾ | M48T512Y | | M48T512V | | Unit |
|------------------|---|----------|-----|----------|-----|------|
| | | -70 | | -85 | | |
| | | Min | Max | Min | Max | |
| t_{AVAV} | READ cycle time | 70 | | 85 | | ns |
| t_{AVQV} | Address valid to output valid | | 70 | | 85 | ns |
| t_{ELQV} | Chip enable low to output valid | | 70 | | 85 | ns |
| t_{GLQV} | Output enable low to output valid | | 40 | | 55 | ns |
| $t_{ELQX}^{(2)}$ | Chip enable low to output transition | 5 | | 5 | | ns |
| $t_{GLQX}^{(2)}$ | Output enable low to output transition | 5 | | 5 | | ns |
| $t_{EHQZ}^{(2)}$ | Chip enable high to output Hi-Z | | 25 | | 30 | ns |
| $t_{GHQZ}^{(2)}$ | Output enable high to output Hi-Z | | 25 | | 30 | ns |
| t_{AXQX} | Address transition to output transition | 10 | | 5 | | ns |

1. Valid for ambient operating temperature: $T_A = 0$ to 70 °C; $V_{CC} = 4.5$ to 5.5 V or 3.0 to 3.6 V (except where noted).

2. $C_L = 5$ pF.

2.2 WRITE mode

The M48T512Y/V is in the WRITE mode whenever \overline{W} (WRITE enable) and \overline{E} (chip enable) are low state after the address inputs are stable.

The start of a WRITE is referenced from the latter occurring falling edge of \overline{W} or \overline{E} . A WRITE is terminated by the earlier rising edge of \overline{W} or \overline{E} . The addresses must be held valid throughout the cycle. \overline{E} or \overline{W} must return high for a minimum of t_{EHAX} from chip enable or t_{WHAX} from WRITE enable prior to the initiation of another READ or WRITE cycle. Data-in must be valid t_{DVWH} prior to the end of WRITE and remain valid for t_{WHDX} afterward. \overline{G} should be kept high during WRITE cycles to avoid bus contention; although, if the output bus has been activated by a low on \overline{E} and \overline{G} a low on \overline{W} will disable the outputs t_{WLQZ} after \overline{W} falls.

Figure 5. WRITE AC waveforms, WRITE enable controlled

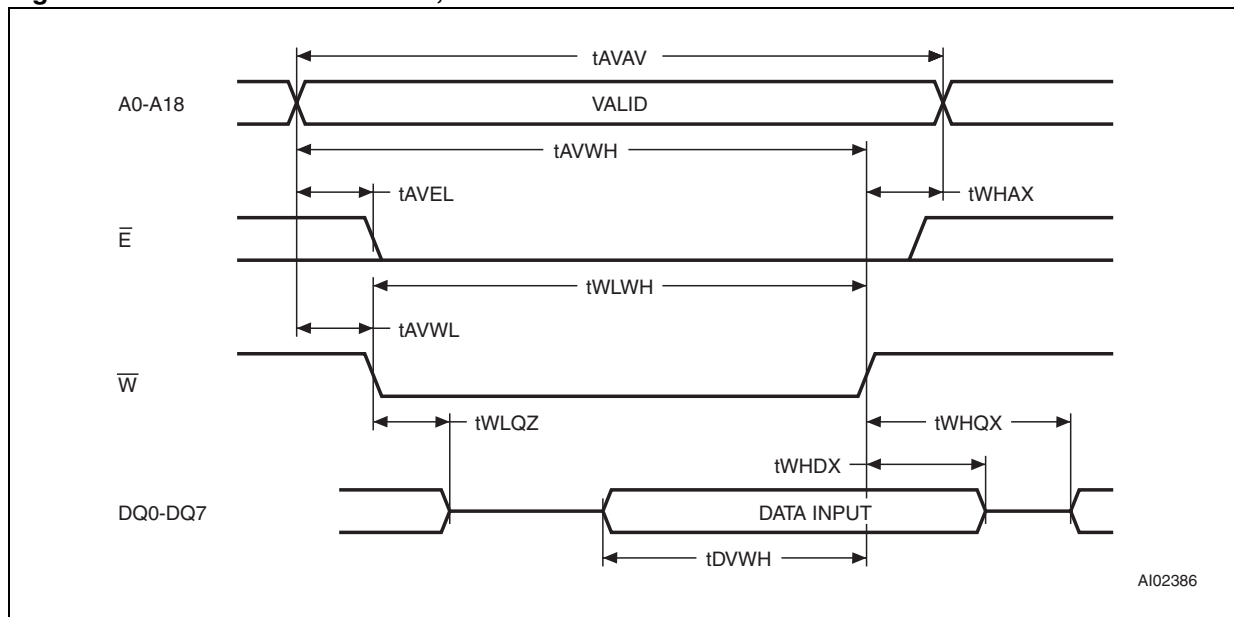


Figure 6. WRITE AC waveforms, chip enable controlled

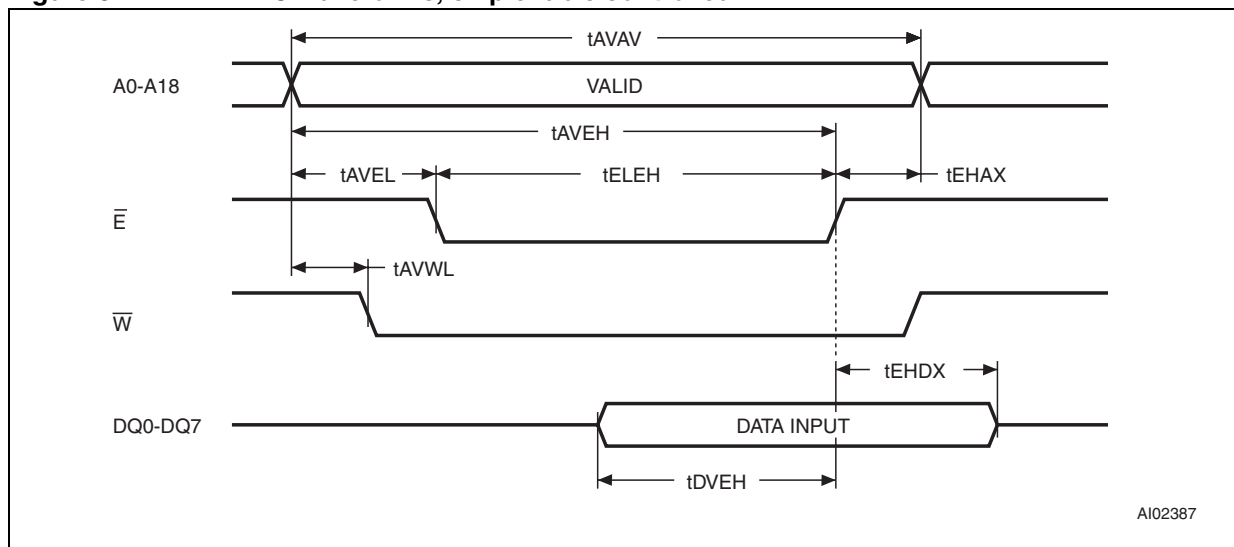


Table 4. WRITE mode AC characteristics

| Symbol | Parameter ⁽¹⁾ | M48T512Y | | M48T512V | | Unit |
|-------------------------------------|---|----------|-----|----------|-----|------|
| | | -70 | | -85 | | |
| | | Min | Max | Min | Max | |
| t _{AVAV} | WRITE cycle time | 70 | | 85 | | ns |
| t _{AVWL} | Address valid to WRITE enable low | 0 | | 0 | | ns |
| t _{AVEL} | Address valid to chip enable low | 0 | | 0 | | ns |
| t _{WLWH} | WRITE enable pulse width | 50 | | 60 | | ns |
| t _{ELEH} | Chip enable low to chip enable high | 55 | | 65 | | ns |
| t _{WHAX} | WRITE enable high to address transition | 5 | | 5 | | ns |
| t _{EHAX} | Chip enable high to address transition | 10 | | 15 | | ns |
| t _{DVWH} | Input valid to WRITE enable high | 30 | | 35 | | ns |
| t _{DVEH} | Input valid to chip enable high | 30 | | 35 | | ns |
| t _{WHDX} | WRITE enable high to input transition | 5 | | 5 | | ns |
| t _{EHDX} | Chip enable high to input transition | 10 | | 15 | | ns |
| t _{WLQZ} ⁽²⁾⁽³⁾ | WRITE enable low to output Hi-Z | | 25 | | 30 | ns |
| t _{AVWH} | Address valid to write enable high | 60 | | 70 | | ns |
| t _{AVEH} | Address valid to chip enable high | 60 | | 70 | | ns |
| t _{WHQX} ⁽²⁾⁽³⁾ | WRITE enable high to output transition | 5 | | 5 | | ns |

- Valid for ambient operating temperature: T_A = 0 to 70 °C; V_{CC} = 4.5 to 5.5 V or 3.0 to 3.6 V (except where noted).
- C_L = 5pF.
- If \bar{E} goes low simultaneously with \bar{W} going low, the outputs remain in the high impedance state.

2.3 Data retention mode

With valid V_{CC} applied, the M48T512Y/V operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically deselect, write protecting itself when V_{CC} falls between V_{PFD} (max) and V_{PFD} (min). All outputs become high impedance and all inputs are treated as “Don't care.”

Note: A power failure during a WRITE cycle may corrupt data at the current addressed location, but does not jeopardize the rest of the RAM's content. At voltages below V_{PFD} (min), the memory will be in a write protected state, provided the V_{CC} fall time is not less than t_F. The M48T512Y/V may respond to transient noise spikes on V_{CC} that cross into the deselect window during the time the device is sampling V_{CC}. Therefore, decoupling of the power supply lines is recommended. When V_{CC} drops below V_{SO}, the control circuit switches power to the internal battery, preserving data and powering the clock. The internal energy source will maintain data in the M48T512Y/V for an accumulated period of at least 10 years at room temperature. As system power rises above V_{SO}, the battery is disconnected, and the power supply is switched to external V_{CC}. Write protection continues until V_{CC} reaches V_{PFD} (min) plus t_{REC} (min). Normal RAM operation can resume t_{REC} after V_{CC} exceeds V_{PFD} (max). Refer to Application Note (AN1012) on the ST website for more information on battery life.

3 Clock operations

3.1 Reading the clock

Updates to the TIMEKEEPER® registers should be halted before clock data is read to prevent reading data in transition (see [Table 5 on page 12](#)). The BiPORT™ TIMEKEEPER cells in the RAM array are only data registers and not the actual clock counters, so updating the registers can be halted without disturbing the clock itself.

Updating is halted when a '1' is written to the READ bit, D6 in the control register (7FFF8h). As long as a '1' remains in that position, updating is halted. After a halt is issued, the registers reflect the count; that is, the day, date, and time that were current at the moment the halt command was issued. All of the TIMEKEEPER registers are updated simultaneously. A halt will not interrupt an update in progress. The next update occurs 1 second after the READ bit is reset to a '0.'

3.2 Setting the clock

Bit D7 of the control register (7FFF8h) is the WRITE bit. Setting the WRITE bit to a '1,' like the READ bit, halts updates to the TIMEKEEPER registers. The user can then load them with the correct day, date, and time data in 24 hour BCD format (see [Table 5 on page 12](#)). Resetting the WRITE bit to a '0' then transfers the values of all time registers 7FFFFh-7FFF9h to the actual TIMEKEEPER counters and allows normal operation to resume. After the WRITE bit is reset, the next clock update will occur approximately one second later.

Note: Upon power-up, both the WRITE bit and the READ bit will be reset to '0.'

3.3 Stopping and starting the oscillator.

The oscillator may be stopped at any time. If the device is going to spend a significant amount of time on the shelf, the oscillator can be turned off to minimize current drain on the battery. The STOP bit is located at bit D7 within 7FFF9h. Setting it to a '1' stops the oscillator. The M48T512Y/V is shipped from STMicroelectronics with the STOP bit set to a '1.' When reset to a '0,' the M48T512Y/V oscillator starts after approximately one second.

Note: It is not necessary to set the WRITE bit when setting or resetting the FREQUENCY TEST bit (FT) or the STOP bit (ST).

Table 5. Register map

| Address | Data | | | | | | | | Function/range BCD format | |
|---------|----------|------------|----------|-------------|---------|-----|----|---------|------------------------------|-------|
| | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 | | |
| 7FFFFh | 10 years | | | | Year | | | | Year | 00-99 |
| 7FFFEh | 0 | 0 | 0 | 10 M | Month | | | | Month | 01-12 |
| 7FFFDh | 0 | 0 | 10 date | | Date | | | | Date | 01-31 |
| 7FFFCCh | 0 | 0 | 0 | 0 | 0 | Day | | | Day | 01-07 |
| 7FFFBh | 0 | 0 | 10 hours | | Hours | | | | Hours | 00-23 |
| 7FFFAh | 0 | 10 minutes | | | Minutes | | | | Minutes | 00-59 |
| 7FFF9h | ST | 10 seconds | | | Seconds | | | | Seconds | 00-59 |
| 7FFF8h | W | R | S | Calibration | | | | Control | | |

Keys:

- S = SIGN bit
- R = READ bit
- W = WRITE bit
- ST = STOP bit
- 0 = Must be set to '0'

3.4 Calibrating the clock

The M48T512Y/V is driven by a quartz controlled oscillator with a nominal frequency of 32,768 Hz. The devices are factory calibrated at 25 °C and tested for accuracy. Clock accuracy will not exceed 35 ppm (parts per million) oscillator frequency error at 25 °C, which equates to about ±1.53 minutes per month. When the Calibration circuit is properly employed, accuracy improves to better than +1/-2 ppm at 25 °C. The oscillation rate of crystals changes with temperature. The M48T512Y/V design employs periodic counter correction. The calibration circuit adds or subtracts counts from the oscillator divider circuit at the divide by 256 stage (see [Figure 8 on page 13](#)).

The number of times pulses are blanked (subtracted, negative calibration) or split (added, positive calibration) depends upon the value loaded into the five calibration bits found in the control register. Adding counts speeds the clock up, subtracting counts slows the clock down. The calibration bits occupy the five lower order bits (D4-D0) in the control register 7FFF8h. These bits can be set to represent any value between 0 and 31 in binary form. Bit D5 is a sign bit; '1' indicates positive calibration, '0' indicates negative calibration. Calibration occurs within a 64 minute cycle. The first 62 minutes in the cycle may, once per minute, have one second either shortened by 128 or lengthened by 256 oscillator cycles. If a binary '1' is loaded into the register, only the first 2 minutes in the 64 minute cycle will be modified; if a binary 6 is loaded, the first 12 will be affected, and so on. Therefore, each calibration step has the effect of adding 512 or subtracting 256 oscillator cycles for every 125, 829, 120 actual oscillator cycles; that is, +4.068 or -2.034 ppm of adjustment per calibration step in the calibration register.

Assuming that the oscillator is running at exactly 32,768 Hz, each of the 31 increments in the calibration byte would represent +10.7 or -5.35 seconds per month which corresponds to a total range of +5.5 or -2.75 minutes per month.

One method for ascertaining how much calibration a given M48T512Y/V may require involves setting the clock, letting it run for a month and comparing it to a known accurate reference and recording deviation over a fixed period of time.

Calibration values, including the number of seconds lost or gained in a given period, can be found in STMicroelectronics' application note AN934, "TIMEKEEPER® calibration." This allows the designer to give the end user the ability to calibrate the clock as the environment requires, even if the final product is packaged in a non-user serviceable enclosure. The designer could provide a simple utility that accesses the calibration bits. For more information on calibration see application note AN934, "TIMEKEEPER® calibration" on the ST website.

Figure 7. Crystal accuracy across temperature

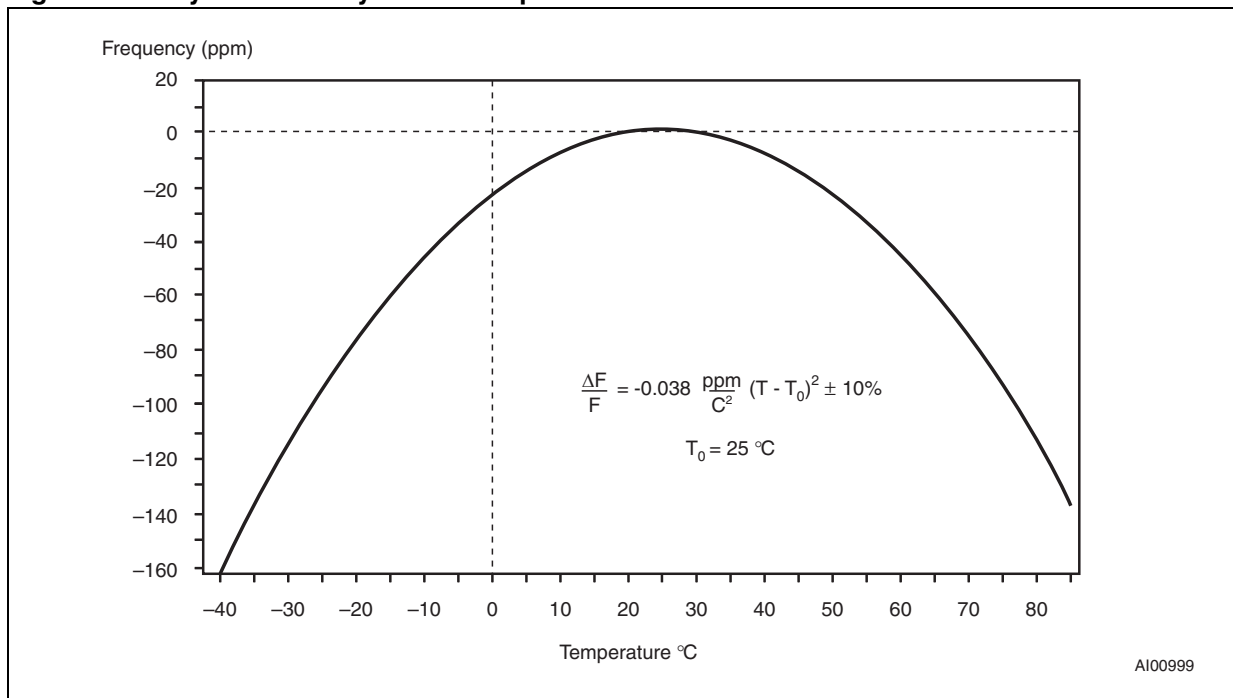
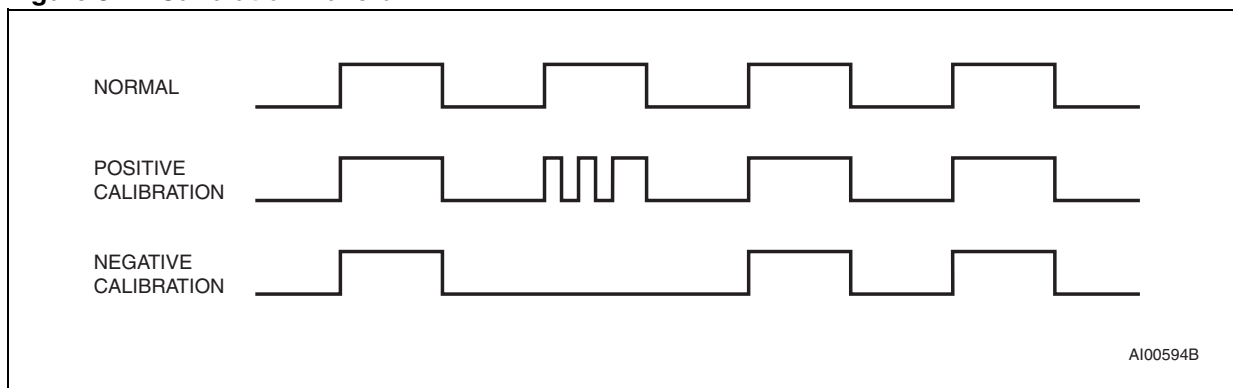


Figure 8. Calibration waveform

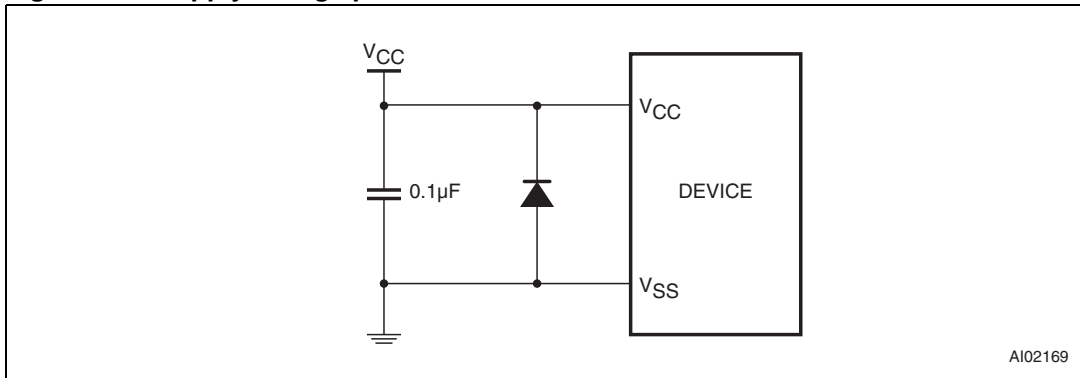


3.5 V_{CC} noise and negative going transients

I_{CC} transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the V_{CC} bus. A ceramic bypass capacitor value of 0.1 μF is recommended to filter these spikes.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on V_{CC} that drive it to values below V_{SS} by as much as one volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, ST recommends connecting a schottky diode from V_{CC} to V_{SS} (cathode connected to V_{CC}, anode to V_{SS}). (Schottky diode 1N5817 is recommended for through hole and MBR5120T3 is recommended for surface mount).

Figure 9. Supply voltage protection



Caution: Negative undershoots below -0.3 V are not allowed on any pin while in the battery backup mode.

4 Maximum ratings

Stressing the device above the ratings listed in the absolute maximum ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 6. Absolute maximum ratings

| Symbol | Parameter | Value | Unit | |
|--------------------|---|------------------------|-------------|---|
| T_A | Ambient operating temperature | 0 to 70 | °C | |
| T_{STG} | Storage temperature (V_{CC} off, oscillator off) | -40 to 85 | °C | |
| $T_{SLD}^{(1)(2)}$ | Lead solder temperature for 10 seconds | 260 | °C | |
| V_{IO} | Input or output voltages | -0.3 to $V_{CC} + 0.3$ | V | |
| V_{CC} | Supply voltage | M48T512Y | -0.3 to 7.0 | V |
| | | M48T512V | -0.3 to 4.6 | V |
| I_O | Output current | 20 | mA | |
| P_D | Power dissipation | 1 | W | |

1. Soldering temperature of the IC leads is to not exceed 260 °C for 10 seconds. In order to protect the lithium battery, preheat temperatures must be limited such that the battery temperature does not exceed +85 °C. Furthermore, the devices shall not be exposed to IR reflow.
2. For DIP packaged devices, ultrasonic vibrations should not be used for post-solder cleaning to avoid damaging the crystal.

Caution: *Negative undershoots below -0.3 V are not allowed on any pin while in the battery backup mode.*

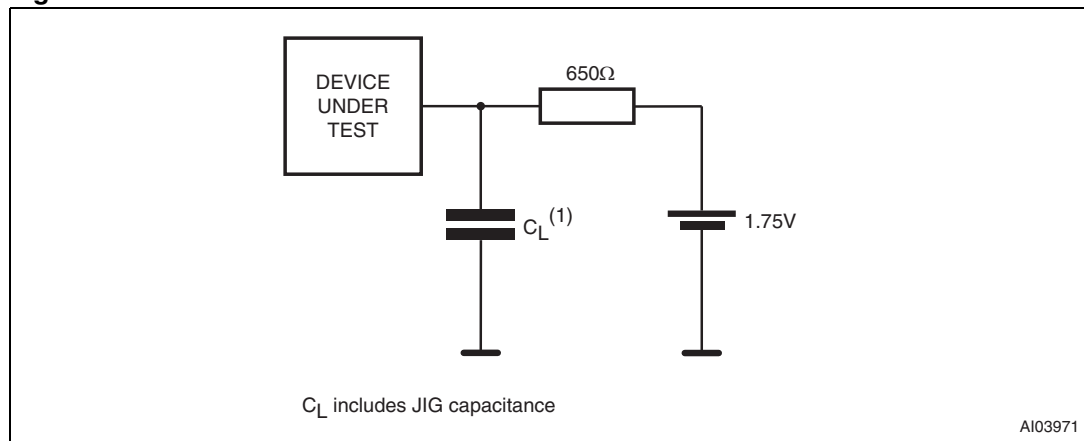
5 DC and AC parameters

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the measurement conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 7. Operating and AC measurement conditions

| Parameter | M48T512Y | M48T512V | Unit |
|---|------------|------------|------|
| Supply voltage (V_{CC}) | 4.5 to 5.5 | 3.0 to 3.6 | V |
| Ambient operating temperature (T_A) | 0 to 70 | 0 to 70 | °C |
| Load capacitance (C_L) | 100 | 50 | pF |
| Input rise and fall times | ≤ 5 | ≤ 5 | ns |
| Input pulse voltages | 0 to 3 | 0 to 3 | V |
| Input and output timing ref. voltages | 1.5 | 1.5 | V |

Figure 10. AC measurement load circuit



1. $C_L = 50$ pF for M48T512V.

Table 8. Capacitance

| Symbol | Parameter ⁽¹⁾⁽²⁾ | Min | Max | Unit |
|----------------|-----------------------------|-----|-----|------|
| C_{IN} | Input capacitance | - | 20 | pF |
| $C_{IO}^{(3)}$ | Input / output capacitance | - | 20 | pF |

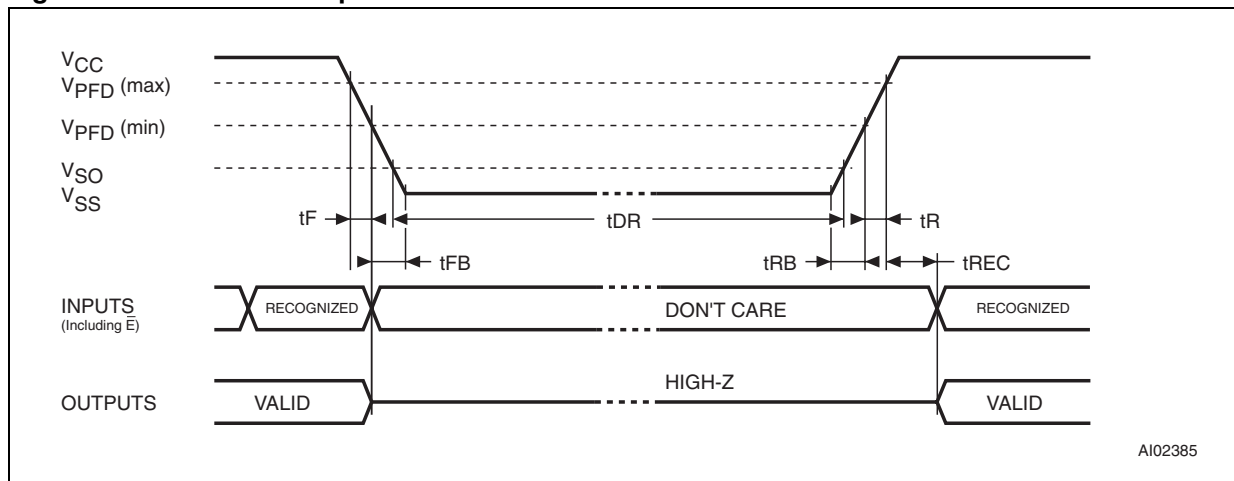
1. Effective capacitance measured with power supply at 5 V (M48T512Y) or 3.3 V (M48T512V). Sampled only, not 100% tested.
2. At 25 °C, $f = 1$ MHz.
3. Outputs deselected.

Table 9. DC characteristics

| Symbol | Parameter | Test condition ⁽¹⁾ | M48T512Y | | M48T512V | | Unit |
|----------------|-------------------------------|--------------------------------|----------|----------------|----------|----------------|------|
| | | | -70 | | -85 | | |
| | | | Min | Max | Min | Max | |
| I_{LI} | Input leakage current | $0 V \leq V_{IN} \leq V_{CC}$ | | ±2 | | ±2 | µA |
| $I_{LO}^{(2)}$ | Output leakage current | $0 V \leq V_{OUT} \leq V_{CC}$ | | ±2 | | ±2 | µA |
| I_{CC} | Supply current | Outputs open | | 115 | | 60 | mA |
| I_{CC1} | Supply current (standby) TTL | $\bar{E} = V_{IH}$ | | 8 | | 4 | mA |
| I_{CC2} | Supply current (standby) CMOS | $\bar{E} \geq V_{CC} - 0.2 V$ | | 4 | | 3 | mA |
| V_{IL} | Input low voltage | | -0.3 | 0.8 | -0.3 | 0.4 | V |
| V_{IH} | Input high voltage | | 2.2 | $V_{CC} + 0.3$ | 2.2 | $V_{CC} + 0.3$ | V |
| V_{OL} | Output low voltage | $I_{OL} = 2.1 mA$ | | 0.4 | | 0.4 | V |
| V_{OH} | Output high voltage | $I_{OH} = -1 mA$ | 2.4 | | 2.2 | | V |

- Valid for ambient operating temperature: $T_A = 0$ to 70 °C; $V_{CC} = 4.5$ to 5.5 V or 3.0 to 3.6 V (except where noted).
- Outputs deselected.

Figure 11. Power down/up mode AC waveforms



AI02385

Table 10. Power down/up AC characteristics

| Symbol | Parameter ⁽¹⁾ | Min | Max | Unit |
|----------------|---|----------|-----|---------|
| $t_F^{(2)}$ | $V_{PFD} (max)$ to $V_{PFD} (min)$ V_{CC} fall time | 300 | | μs |
| $t_{FB}^{(3)}$ | $V_{PFD} (min)$ to V_{SS} V_{CC} fall time | M48T512Y | 10 | μs |
| | | M48T512V | 150 | μs |
| t_R | $V_{PFD} (min)$ to $V_{PFD} (max)$ V_{CC} rise time | 10 | | μs |
| t_{RB} | V_{SS} to $V_{PFD} (min)$ V_{CC} rise time | 1 | | μs |
| t_{REC} | \bar{E} recovery time | 40 | 200 | ms |

- Valid for ambient operating temperature: $T_A = 0$ to 70 °C; $V_{CC} = 4.5$ to 5.5 V or 3.0 to 3.6 V (except where noted).
- $V_{PFD} (max)$ to $V_{PFD} (min)$ fall time of less than t_F may result in deselection/write protection not occurring until $200\mu s$ after V_{CC} passes $V_{PFD} (min)$.
- $V_{PFD} (min)$ to V_{SS} fall time of less than t_{FB} may cause corruption of RAM data.

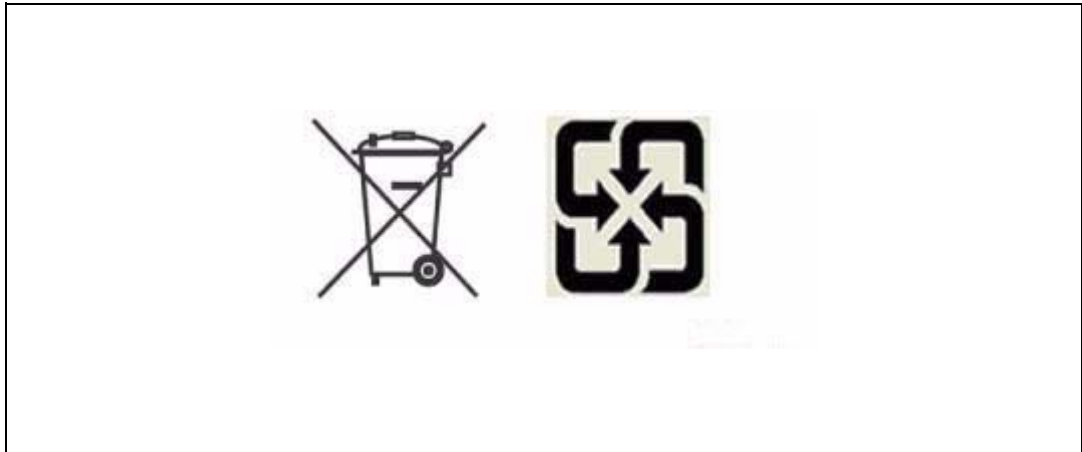
Table 11. Power down/up trip points DC characteristics

| Symbol | Parameter ⁽¹⁾⁽²⁾ | Min | Typ | Max | Unit | |
|----------------|-----------------------------------|----------|-----|-------------------|-------|---|
| V_{PFD} | Power-fail deselect voltage | M48T512Y | 4.2 | 4.35 | 4.5 | V |
| | | M48T512V | 2.7 | 2.9 | 3.0 | V |
| V_{SO} | Battery backup switchover voltage | M48T512Y | | 3.0 | | V |
| | | M48T512V | | $V_{PFD} - 100mV$ | | V |
| $t_{DR}^{(3)}$ | Expected data retention time | 10 | | | YEARS | |

- All voltages referenced to V_{SS} .
- Valid for ambient operating temperature: $T_A = 0$ to 70 °C; $V_{CC} = 4.5$ to 5.5 V or 3.0 to 3.6 V (except where noted).
- At 25 °C, $V_{CC} = 0$ V.

6 Environmental information

Figure 12. Recycling symbols



This product contains a non-rechargeable lithium (lithium carbon monofluoride chemistry) button cell battery fully encapsulated in the final product.

Recycle or dispose of batteries in accordance with the battery manufacturer's instructions and local/national disposal and recycling regulations.

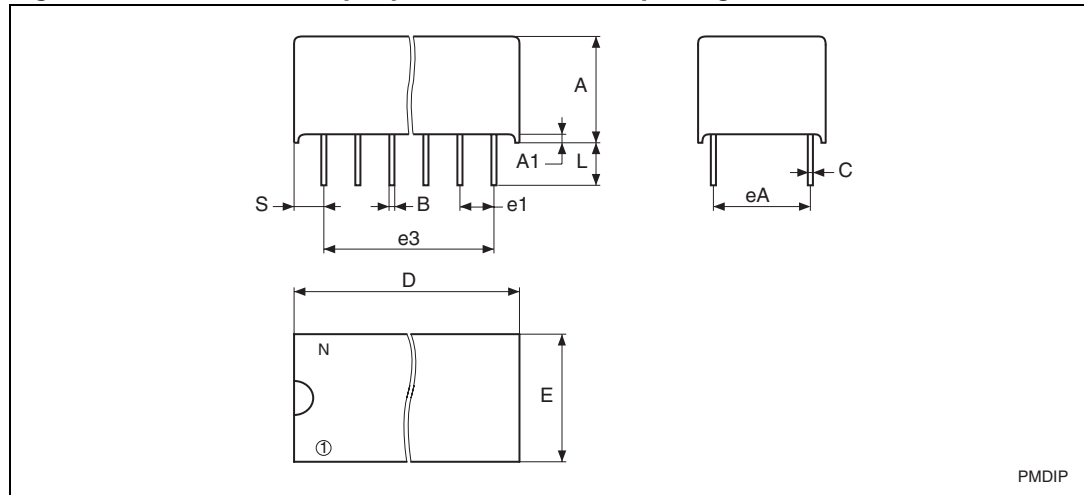
Please refer to the following web site address for additional information regarding compliance statements and waste recycling.

Go to www.st.com/nvram, then select "Lithium Battery Recycling" from "Related Topics".

7 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 13. PMDIP32 – 32-pin plastic module DIP, package outline



Note: Drawing is not to scale.

Table 12. PMDIP32 – 32-pin plastic module DIP, package mechanical data

| Symb | mm | | | inches | | |
|------|------|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | 9.27 | 9.52 | | 0.365 | 0.375 |
| A1 | | 0.38 | – | | 0.015 | – |
| B | | 0.43 | 0.59 | | 0.017 | 0.023 |
| C | | 0.20 | 0.33 | | 0.008 | 0.013 |
| D | | 42.42 | 43.18 | | 1.670 | 1.700 |
| E | | 18.03 | 18.80 | | 0.710 | 0.740 |
| e1 | | 2.29 | 2.79 | 0.100 | 0.090 | 0.110 |
| e3 | 38.1 | | | 1.500 | | |
| eA | | 14.99 | 16.00 | 0.600 | 0.590 | 0.630 |
| L | | 3.05 | 3.81 | | 0.120 | 0.150 |
| S | | 1.91 | 2.79 | | 0.075 | 0.110 |
| N | | 32 | | | 32 | |

8 Part numbering

Table 13. Ordering information scheme

| Example: | M48T | 512Y | -70 | PM | 1 |
|---|------|---|--|--------------|---|
| Device type | M48T | | | | |
| Supply voltage and write protect voltage | | 512Y = V _{CC} = 4.5 to 5.5 V; V _{PFD} = 4.2 to 4.5 V 512V ⁽¹⁾ = V _{CC} = 3.0 to 3.6 V; V _{PFD} = 2.7 to 3.0 V | | | |
| Speed | | | -70 = 70 ns (512Y) -85 = 85 ns (512V) | | |
| Package | | | | PM = PMDIP32 | |
| Temperature range | | | | | 1 = 0 to 70 °C |
| Shipping method | | | | | Blank = ECOPACK [®] package, tubes |

1. Contact the local ST sales office for availability.

For other options, or for more information on any aspect of this device, please contact the ST sales office nearest you.

9 Revision history

Table 14. Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| June-1998 | 1 | First issue |
| 03-Dec-1999 | 1.1 | M48T512Y: V_{PFD} (Min) changed; AC measurement load circuit changed (Figure 10); t_{FB} and t_{RB} changed (Figure 11 , Table 10) |
| 11-Dec-2000 | 2 | Reformatted |
| 20-Jul-2001 | 2.1 | Segments re-ordered; temp./voltage info. added to tables (Table 8 , 9 , 3 , 4 , 10 , 11) |
| 07-Aug-2001 | 2.2 | Text re-ordered from last adjustment (“Operating modes” section) |
| 20-May-2002 | 2.3 | Add countries to disclaimer |
| 07-Aug-2002 | 2.4 | Add marketing status |
| 31-Mar-2003 | 3 | v2.2 template applied; data retention condition updated (Table 11) |
| 22-Feb-2005 | 4 | Reformatted; IR reflow update (Table 6) |
| 25-Mar-2008 | 5 | Reformatted document, minor text changes; updated cover page and Table 13 concerning availability of M48T512V (3.3 V version); updated Figure 9 , 10 , 11 , Table 9 , 12 , Section 7: Package mechanical data . |
| 21-Jun-2010 | 6 | Updated Features , Section 4 , Table 12 , 13 ; text in Section 7 ; added Section 6: Environmental information ; reformatted document. |

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